



TR 2N6491(=BDP396);CYD;TO220;tranz. PNP;15A;90V;75W;>5MHz;RoHS



Dane techniczne:

Nazwa: 2N6491(=BDP396)

Typ tranzystora: bipolarny

Kierunek przewodnictwa: PNP

Prąd kolektora: 15A

Napięcie kolektor-emiter: 90V

Moc: 75W

Częstotliwość: >5MHz

Obudowa: TO220

Montaż: przewlekany (THT)



COMPLEMENTARY SILICON POWER TRANSISTORS

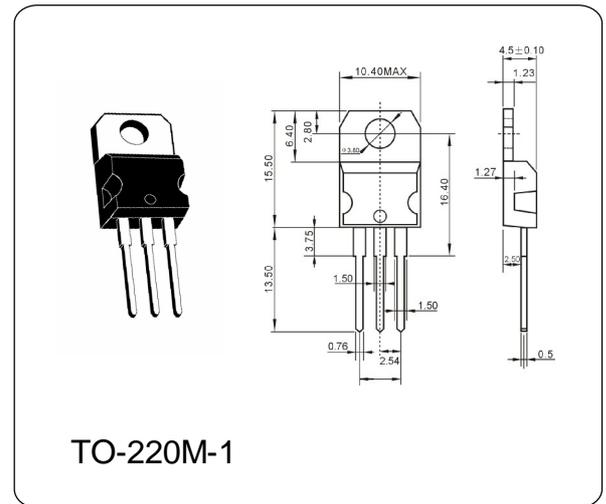
2N6491

DESCRIPTION

The 2N6491 is silicon epitaxial-base PNP transistors in Jedec TO-220 plastic package. They are intended for use in power linear and low frequency switching applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-90	V
Collector-Emitter Voltage	V_{CEO}	-90	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	15	A
Base Current	I_B	5.0	A
Total Dissipation at	P_{tot}	75	W
Max. Operating Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cut-off Current	I_{CEO}	$V_{CB} = -80V, I_E = 0$	—	—	0.3	mA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	1.0	mA
Collector-Emitter Sustaining Voltage	V_{CEO}	$I_C = 10mA, I_B = 0$	80	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -4V, I_C = 0.5A$	50	—	—	
	$h_{FE(2)}$	$V_{CE} = -4V, I_C = 1.0A$	80	—	200	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 5.0A, I_B = 500mA$	—	—	-1.2	V
Base-Emitter Voltage	$V_{BE(sat)}$	$I_C = 5.0A, I_B = 500mA$	—	—	-2.0	V
Current Gain Bandwidth Product	f_T	$V_{CE} = -4.0V, I_C = 500mA$	4	—	—	MHz